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Renesas Electronics website: http://www.renesas.com

April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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# 2SC5849

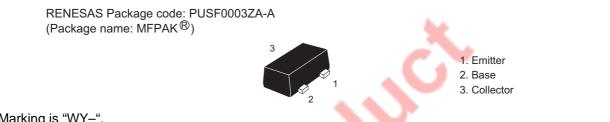
# Silicon NPN Epitaxial VHF/UHF wide band amplifier

REJ03G0759-0100 (Previous ADE-208-1469) Rev.1.00 Aug.10.2005

### **Features**

Super compact package: MFPAK (1.4 x 0.8 x 0.59 mm)

### Outline



Note: Marking is "WY-".

\*MFPAK is a trademark of Renesas Technology Corp.

# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	15	V
Collector to emitter voltage	V <sub>CEO</sub>	6.0	V
Emitter to base voltage	V <sub>EBO</sub>	1.5	V
Collector current	Ι <sub>C</sub>	80	mA
Collector power dissipation	Pc	80	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to 150	°C

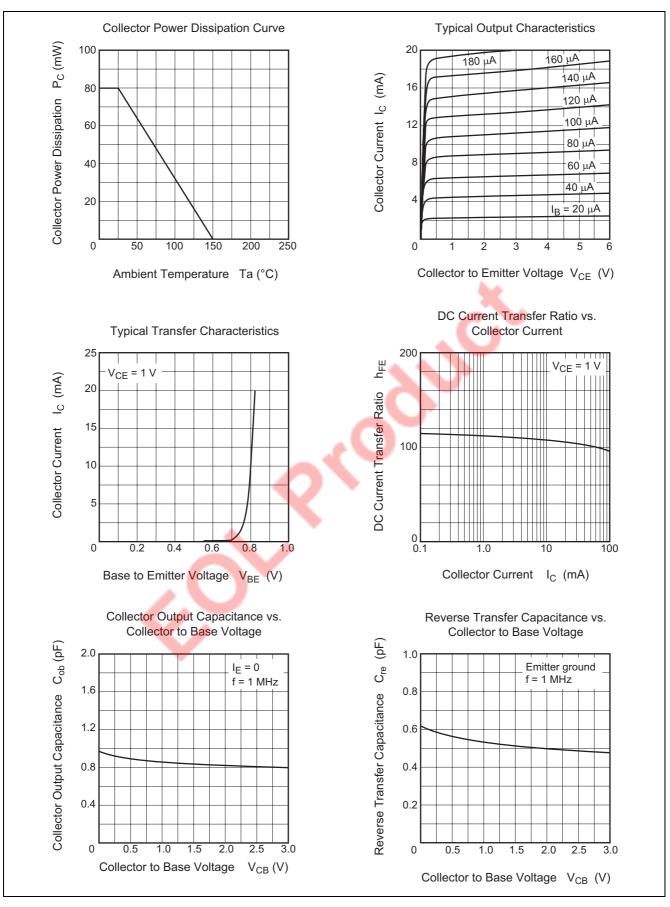


# **Electrical Characteristics**

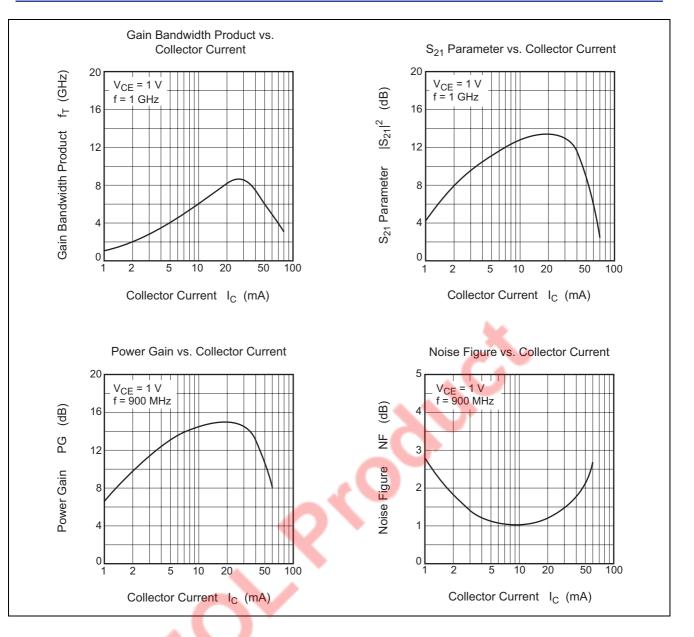
Collector to base breakdown voltage $V_{(BR)CBO}$ 15V $l_{c} = 10 \ \mu$ A, $l_{E} = 0$ Collector cutoff current $l_{CBO}$ 0.1 $\mu$ A $V_{CB} = 15 \ V$ , $l_{E} = 0$ Collector cutoff current $l_{CEO}$ 0.1 $\mu$ A $V_{CB} = 15 \ V$ , $l_{E} = 0$ Emitter cutoff current $l_{EBO}$ 0.1 $\mu$ A $V_{CE} = 6.0 \ V$ , $R_{BE} = \infty$ Emitter cutoff current $l_{EBO}$ 0.1 $\mu$ A $V_{CE} = 10 \ V$ , $l_{C} = 10 \ \mu$ A, $l_{E} = 0$ DC current transfer ratio $h_{FE}$ 90110140 $V_{CE} = 6.0 \ V$ , $R_{BE} = \infty$ Reverse transfer capacitance $C_{re}$ 0.5 $PF$ Collector output capacitance $C_{ob}$ 0.851.15 $pF$ $V_{CE} = 1 \ V$ , $l_{C} = 5 \ mA$ Gain bandwidth product $f_{T}(1)$ 1.04.0 $GHz$ $V_{CE} = 1 \ V$ , $l_{C} = 5 \ mA$ Gain bandwidth product $f_{T}(2)$ 9.0 $GHz$ $V_{CE} = 1 \ V$ , $l_{C} = 5 \ mA$ Power gainPG1013 $dB$ $V_{CE} = 1 \ V$ , $l_{C} = 5 \ mA$ , $f = 900 \ MHz$ Noise figureNF1.11.8 $dB$ $V_{CE} = 1 \ V$ , $l_{C} = 5 \ mA$ , $f = 900 \ MHz$	Item	Symbol	Min	Тур	Max	Unit	Test conditions
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	15	_	—	V	$I_{C} = 10 \ \mu A, I_{E} = 0$
Emitter cutoff currentII <t< td=""><td>Collector cutoff current</td><td></td><td></td><td>_</td><td>0.1</td><td>μΑ</td><td><math>V_{CB} = 15 \text{ V}, I_E = 0</math></td></t<>	Collector cutoff current			_	0.1	μΑ	$V_{CB} = 15 \text{ V}, I_E = 0$
DC current transfer ratio $h_{FE}$ 90110140 $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$ Reverse transfer capacitance $C_{re}$ $ 0.5$ $ pF$ $V_{CE} = 1 \text{ V}, \text{ Emitter ground,}$ Collector output capacitance $C_{ob}$ $ 0.85$ $1.15$ $pF$ $V_{CE} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ Collector output capacitance $f_{T}(1)$ $1.0$ $4.0$ $ GHz$ $V_{CE} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ Gain bandwidth product $f_{T}(2)$ $ 9.0$ $ GHz$ $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 30 \text{ mA}$ Gain bandwidth product $f_{T}(2)$ $ 9.0$ $ GHz$ $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 30 \text{ mA}$ Power gainPG $10$ $13$ $ dB$ $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA},$ Noise figureNF $ 1.1$ $1.8$ $dB$ $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA},$	Collector cutoff current	I <sub>CEO</sub>	—	—	0.1	μA	$V_{CE}$ = 6.0 V, $R_{BE}$ = $\infty$
Reverse transfer capacitance $C_{re}$ $ 0.5$ $ pF$ $V_{CE} = 1 \text{ V}$ , Emitter ground, f = 1 MHzCollector output capacitance $C_{ob}$ $ 0.85$ $1.15$ $pF$ $V_{CB} = 1 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$ Gain bandwidth product $f_T(1)$ $1.0$ $4.0$ $ GHz$ $V_{CE} = 1 \text{ V}$ , $I_C = 5 \text{ mA}$ Gain bandwidth product $f_T(2)$ $ 9.0$ $ GHz$ $V_{CE} = 1 \text{ V}$ , $I_C = 30 \text{ mA}$ Power gainPG $10$ $13$ $ dB$ $V_{CE} = 1 \text{ V}$ , $I_C = 5 \text{ mA}$ , $f = 900 \text{ MHz}$ Noise figureNF $ 1.1$ $1.8$ $dB$ $V_{CE} = 1 \text{ V}$ , $I_C = 5 \text{ mA}$ ,	Emitter cutoff current	I <sub>EBO</sub>	_	_	0.1	μΑ	$V_{EB} = 1.5 V, I_C = 0$
Collector output capacitance $C_{ob}$ $0.85$ $1.15$ pF $V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ Gain bandwidth product $f_T(1)$ $1.0$ $4.0$ $GHz$ $V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}$ Gain bandwidth product $f_T(2)$ $9.0$ $GHz$ $V_{CE} = 1 \text{ V}, I_C = 30 \text{ mA}$ Power gain         PG $10$ $13$ $dB$ $V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 900 \text{ MHz}$ Noise figure         NF $1.1$ $1.8$ $dB$ $V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 900 \text{ MHz}$	DC current transfer ratio	h <sub>FE</sub>	90	110	140		$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Reverse transfer capacitance	C <sub>re</sub>		0.5	_	pF	
Gain bandwidth product $f_T(2)$ —         9.0         —         GHz $V_{CE} = 1 \text{ V}, \text{ I}_C = 30 \text{ mA}$ Power gain         PG         10         13         —         dB $V_{CE} = 1 \text{ V}, \text{ I}_C = 5 \text{ mA},$ Noise figure         NF         —         1.1         1.8         dB $V_{CE} = 1 \text{ V}, \text{ I}_C = 5 \text{ mA},$	Collector output capacitance	C <sub>ob</sub>	_	0.85	1.15	pF	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Power gain         PG         10         13         —         dB $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA},$ Noise figure         NF         —         1.1         1.8         dB $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA},$	Gain bandwidth product	f⊤(1)	1.0	4.0		GHz	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$
Image: Noise figure         NF          1.1         1.8         dB         V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA,	Gain bandwidth product	f <sub>T</sub> (2)	_	9.0		GHz	$V_{CE} = 1 \text{ V}, I_{C} = 30 \text{ mA}$
	Power gain	PG	10	13	—	dB	
	Noise figure	NF		1.1	1.8	dB	
		<	24	0	9		



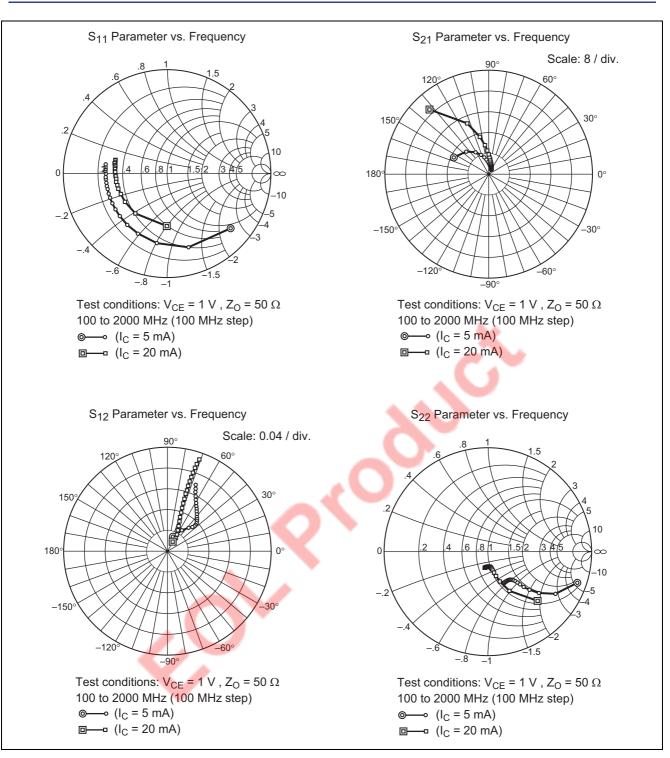
### **Main Characteristics**













### **S** Parameter

 $(V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, Z_O = 50 \Omega)$ 

	S11		S21		S12		S22	
f (MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.807	-40.6	14.95	154.2	0.030	69.3	0.913	-19.1
200	0.737	-73.7	12.30	135.0	0.049	55.5	0.768	-31.8
300	0.675	-98.4	9.86	121.2	0.061	47.8	0.633	-38.8
400	0.642	-115.9	8.03	111.9	0.067	44.0	0.544	-42.3
500	0.624	-127.9	6.72	105.0	0.071	42.8	0.484	-44.4
600	0.611	-138.1	5.75	99.4	0.074	43.2	0.442	-45.2
700	0.604	-145.4	5.02	95.0	0.078	43.8	0.412	-46.0
800	0.599	-151.6	4.45	90.9	0.081	45.4	0.390	-46.7
900	0.595	-157.2	3.98	87.6	0.084	47.2	0.373	-47.6
1000	0.594	-161.2	3.62	84.5	0.087	49.3	0.362	-48.4
1100	0.591	-165.5	3.33	81.8	0.091	51 <mark>.3</mark>	0.354	-49.5
1200	0.592	-168.4	3.06	79.0	0.095	53.6	0.347	-50.7
1300	0.591	-171.5	2.86	76.4	0.099	55.3	0.341	-52.0
1400	0.592	-174.8	2.66	74.1	0.103 🧹	57.2	0.340	-53.5
1500	0.592	-176.8	2.51	72.0	0.108	59.1	0.335	-54.8
1600	0.589	-180.0	2.35	69.7	0.113	61.1	0.337	-56.3
1700	0.594	177.7	2.23	67.8	0.119	62.8	0.334	-58.3
1800	0.594	175.7	2.13	65.7	0.126	64.7	0.335	-60.0
1900	0.596	173.9	2.03	63.7	0.132	65.7	0.335	-62.0
2000	0.598	171.3	1.94	61.9	0.139	66.9	0.335	-64.0

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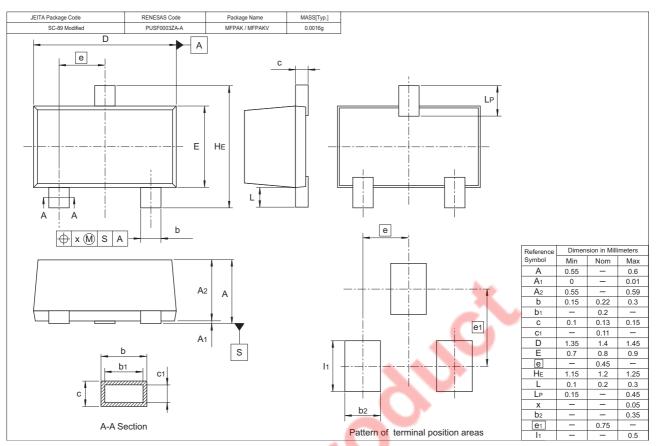


						$(\mathbf{v}_{CE} \equiv \mathbf{I})$	$V, I_C = 20 \text{ m/}$	$A, Z_0 = 50 \Omega)$
S11		S21		S12		\$22		
f (MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.504	-90.3	33.79	132.5	0.021	61.4	0.674	-44.5
200	0.490	-128.6	21.25	112.9	0.030	57.6	0.431	-61.0
300	0.488	-146.2	14.78	103.3	0.037	60.2	0.309	-67.9
400	0.487	-156.3	11.31	97.4	0.045	63.7	0.247	-71.1
500	0.492	-162.8	9.13	93.3	0.053	66.0	0.210	-73.2
600	0.492	-167.0	7.65	90.0	0.062	68.0	0.187	-75.1
700	0.497	-170.8	6.58	87.2	0.070	69.6	0.171	-76.7
800	0.492	-174.1	5.78	84.4	0.079	70.4	0.160	-78.2
900	0.496	-177.0	5.13	82.6	0.088	71.2	0.152	-79.9
1000	0.498	-178.4	4.65	80.2	0.097	71.7	0.147	-81.4
1100	0.500	178.2	4.24	78.3	0.106	72.0	0.145	-83.2
1200	0.503	177.5	3.90	76.1	0.116	72.4	0.143	-85.1
1300	0.503	175.2	3.63	74.3	0.123	72.1	0.143	-87.2
1400	0.506	173.7	3.38	72.6	0.132	72.4	0.144	-88.8
1500	0.503	172.0	3.17	70.9	0.141	72.3	0.144	-91.2
1600	0.507	170.6	2.99	69.4	0.150	72.1	0.146	-92.8
1700	0.516	168.9	2.82	67.7	0.159	72.0	0.148	-95.0
1800	0.511	167.3	2.68	66.0	0.169	71.7	0.151	-97.0
1900	0.515	165.6	2.56	64.6	0.177	71.4	0.154	-99.0
2000	0.514	165.1	2.45	63.0	0.187	70.8	0.158	-100.8

 $(V_{CE} = 1 \text{ V}, I_C = 20 \text{ mA}, Z_O = 50 \Omega)$ 



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